Analog Power AM60N10-70P

N-Channel 100-V (D-S) MOSFET

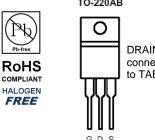
Key Features:

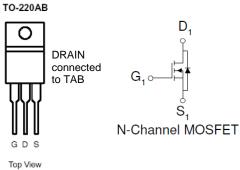
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
100	78 @ V _{GS} = 10V	51 ^a	
100	92 @ $V_{GS} = 5.5V$	51	





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			100	V		
Gate-Source Voltage		V_{GS}	±20	ľ		
Continuous Drain Current a	T _A =25°C	I_D	51	А		
Pulsed Drain Current ^b		I _{DM}	240 A			
Continuous Source Current (Diode Conduction) a			90	Α		
Power Dissipation ^a	T _A =25°C	P_{D}	300	W		
Operating Junction and Storage Temperature Range	·	T_J, T_{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	62.5	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	1	C/VV

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Notes

- Surface Mounted on 1" x 1" FR4 Board. a.
- Pulse width limited by maximum junction temperature b.

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Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	100			Α
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			78	mΩ
	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, I_D = 18 \text{ A}$			92	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		25		S
Diode Forward Voltage	V_{SD}	$I_{S} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		0.93		V
		Dynamic				
Total Gate Charge	Q_g	$V_{DS} = 50 \text{ V}, V_{GS} = 5.5 \text{ V},$ $I_{D} = 20 \text{ A}$		13		nC
Gate-Source Charge	Q_{gs}			4.3		
Gate-Drain Charge	Q_gd			8.2		
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 50 \text{ V}, R_{L} = 2.5 \Omega,$ $I_{D} = 20 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		9		ns
Rise Time	t _r			9		
Turn-Off Delay Time	$t_{d(off)}$			20		
Fall Time	t _f			11		
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		822		pF
Output Capacitance	C _{oss}			83		
Reverse Transfer Capacitance	C_{rss}			72		

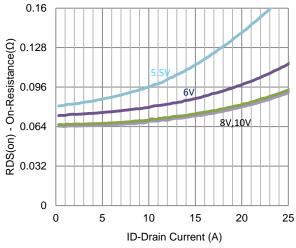
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

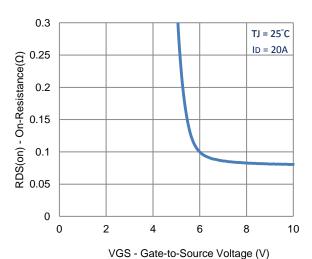
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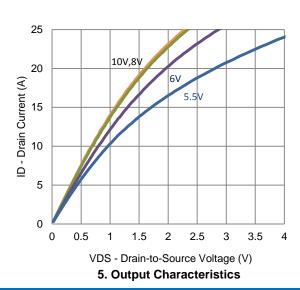
Typical Electrical Characteristics

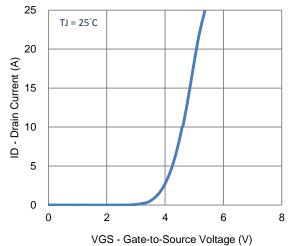


1. On-Resistance vs. Drain Current

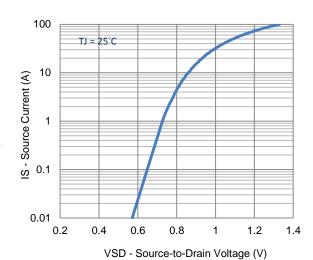


3. On-Resistance vs. Gate-to-Source Voltage

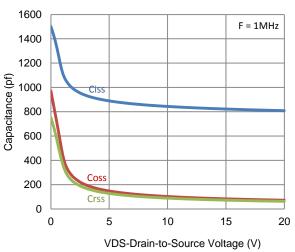




2. Transfer Characteristics



4. Drain-to-Source Forward Voltage



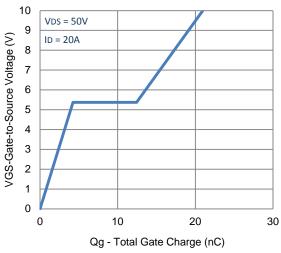
6. Capacitance

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Typical Electrical Characteristics

2.5

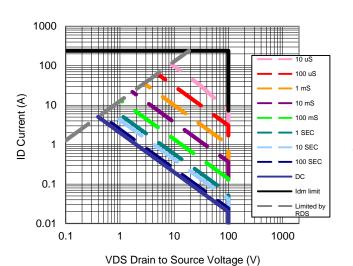
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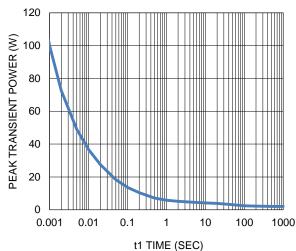
 $RDS(on) - On-Resistance(\Omega) \\ (Normalized)$ 1.5 0.5 -50 -25 0 25 50 75 100 125 150 175

TJ -JunctionTemperature(°C)

7. Gate Charge

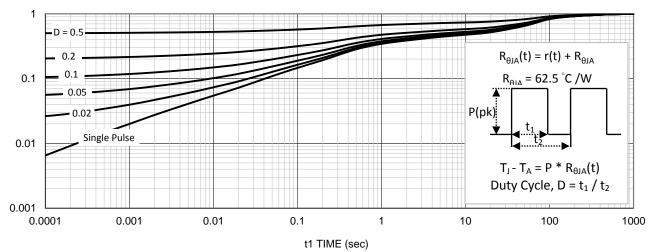


8. Normalized On-Resistance Vs **Junction Temperature**



9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

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Package Information

